

## 2N4117/A, 2N4118/A, 2N4119/A N-Channel JFET

### Features

- InterFET [N0001H Geometry](#)
- Low Leakage: 0.25 pA Typical
- Low Input Capacitance: 2.0 pF Typical
- High Input Impedance
- RoHS Compliant
- SMT, TH, and Bare Die Package options.

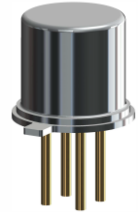
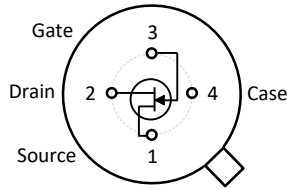
### Applications

- Low Leakage Input Buffer
- High Frequency Amplifier/Buffer
- Ultrahigh Impedance Pre-Amplifier
- Voltage Controlled Resistor
- Current Limiters and Regulators

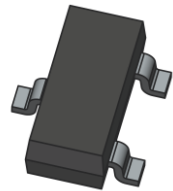
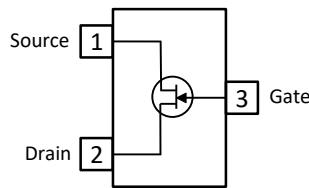
### Description

The -50V InterFET 2N4117/A, 2N4118/A, and 2N4119/A JFET's are targeted for ultra high input impedance applications for mid to high frequency designs. Gate leakages are typically 1pA at room temperatures. The 2N4117 has a cutoff voltage of less than 1.8V ideal for low-level power supplies. The TO-72 package is hermetically sealed and suitable for military applications.

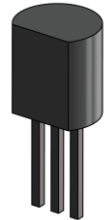
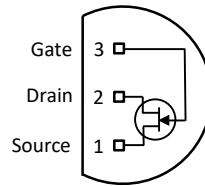
TO-72 Bottom View



SOT23 Top View



TO-92 Bottom View



### Product Summary

Parameters	2N4117/A Min	2N4118/A Min	2N4119/A Min	Unit
BV <sub>GSS</sub> Gate to Source Breakdown Voltage	-40	-40	-40	V
I <sub>DSS</sub> Drain to Source Saturation Current	0.03	0.08	0.2	mA
V <sub>GS(off)</sub> Gate to Source Cutoff Voltage	-0.6	-1	-2	V
G <sub>FS</sub> Forward Transconductance	70	80	100	μS

### Ordering Information Custom Part and Binning Options Available

Part Number	Description	Case	Packaging
2N4117; 2N4118; 2N4119 2N4117A; 2N4118A; 2N4119A	Through-Hole	TO-72	Bulk
PN4117; PN4118; PN4119 PN4117A; PN4118A; PN4119A	Through-Hole	TO-92	Bulk
SMP4117; SMP4118; SMP4119 SMP4117A; SMP4118A; SMP4119A	Surface Mount	SOT23	Bulk
SMP4117TR; SMP4118TR; SMP4119TR SMP4117ATR; SMP4118ATR; SMP4119ATR	7" Tape and Reel: Max 3,000 Pieces 13" Tape and Reel: Max 9,000 Pieces	SOT23	Minimum 1,000 Pieces Tape and Reel
2N4117COT; 2N4118COT; 2N4119COT	Chip Orientated Tray (COT Waffle Pack)	COT	400/Waffle Pack
2N4117CFT; 2N4118CFT; 2N4119CFT	Chip Face-up Tray (CFT Waffle Pack)	CFT	400/Waffle Pack



**Disclaimer:** It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.

## Electrical Characteristics

### Maximum Ratings (@ $T_A = 25^\circ\text{C}$ , Unless otherwise specified)

Parameters	Value	Unit
$V_{RGS}$ Reverse Gate Source and Gate Drain Voltage	-40	V
$I_{FG}$ Continuous Forward Gate Current	50	mA
$P_D$ Continuous Device Power Dissipation	300	mW
$P$ Power Derating	2	mW/ $^\circ\text{C}$
$T_J$ Operating Junction Temperature	-55 to 125	$^\circ\text{C}$
$T_{STG}$ Storage Temperature	-65 to 150	$^\circ\text{C}$

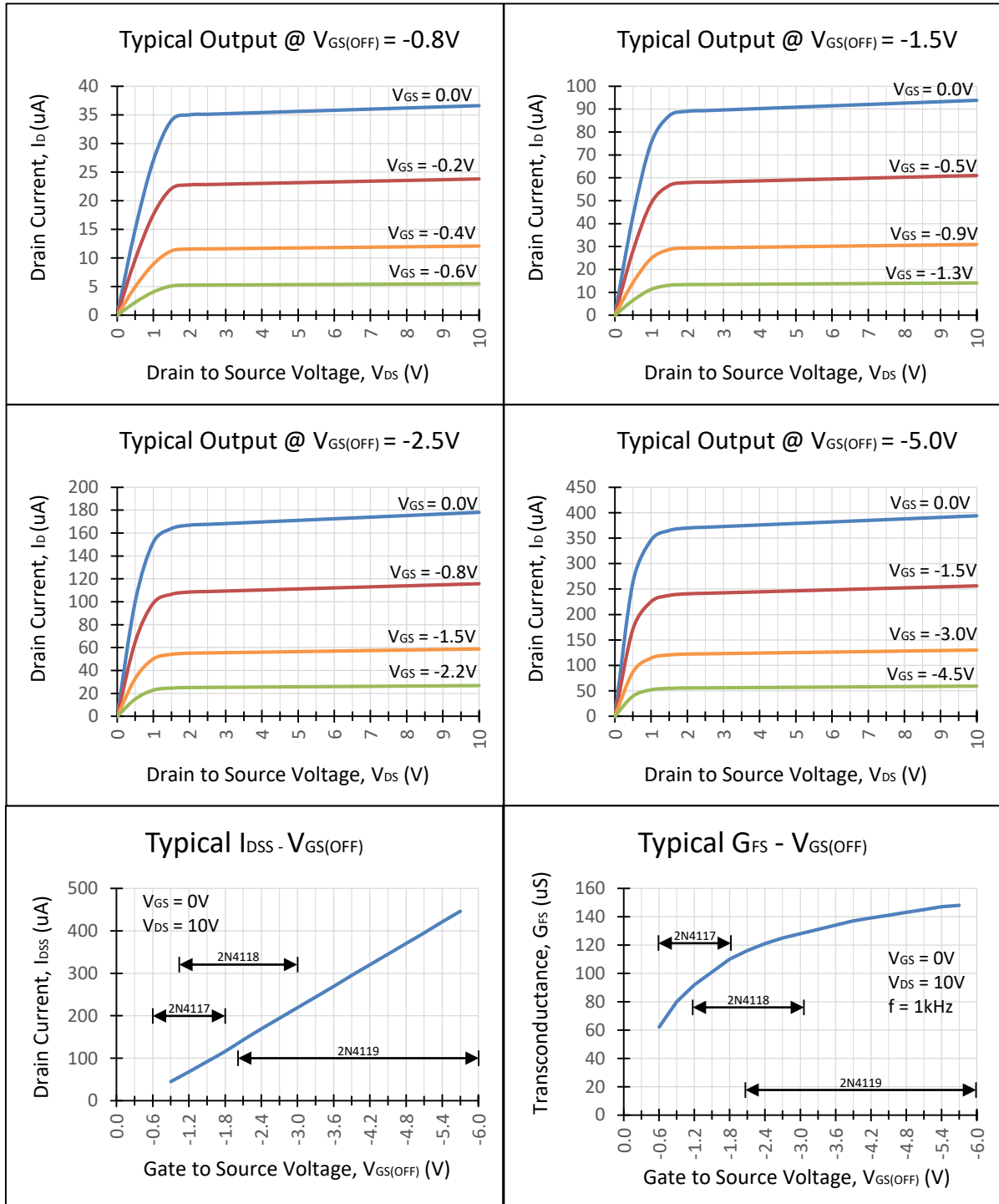
### Static Characteristics (@ $T_A = 25^\circ\text{C}$ , Unless otherwise specified, Highlighted values = A variant)

Parameters	Conditions	2N4117/A		2N4118/A		2N4119/A		Unit
		Min	Max	Min	Max	Min	Max	
$V_{(BR)GSS}$ Gate to Source Breakdown Voltage	$I_G = -1\mu\text{A}, V_{DS} = 0\text{V}$	-40		-40		-40		V
$I_{GSS}$ Gate to Source Reverse Current	$V_{GS} = -20\text{V}, V_{DS} = 0\text{V}$		-10		-10		-10	pA
			-1		-1		-1	pA
$V_{GS(OFF)}$ Gate to Source Cutoff Voltage	$V_{DS} = 10\text{V}, I_D = 1\text{nA}$	-0.6	-1.8	-1	-3	-2	-6	V
$I_{DSS}$ Drain to Source Saturation Current	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}$ (Pulsed)	0.03	0.09	0.08	0.24	0.2	0.6	mA
		0.015	0.09	0.08	0.24	0.2	0.6	mA

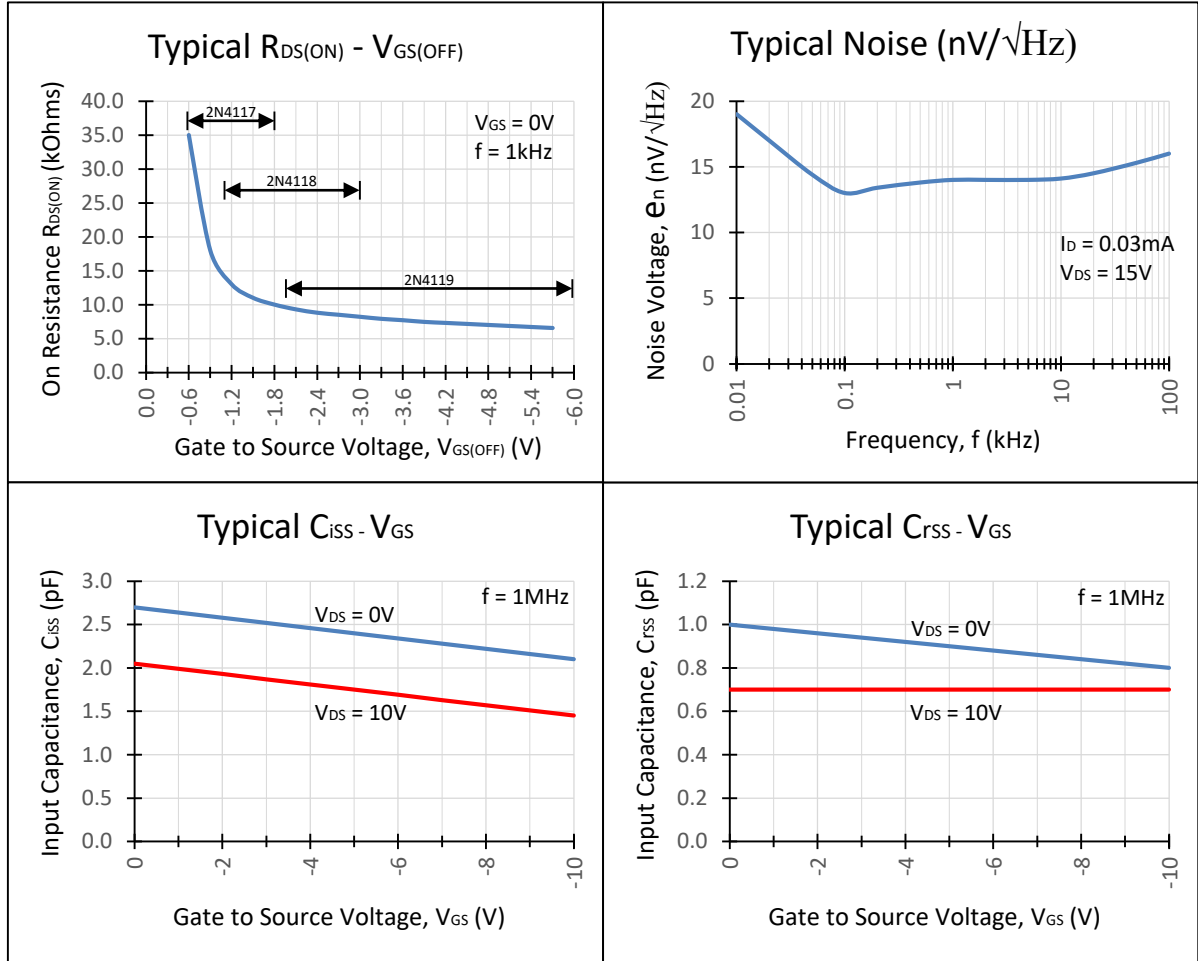
### Dynamic Characteristics (@ $T_A = 25^\circ\text{C}$ , Unless otherwise specified)

Parameters	Conditions	2N4117/A		2N4118/A		2N4119/A		Unit
		Min	Max	Min	Max	Min	Max	
$G_{FS}$ Forward Transconductance	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1\text{kHz}$	70	210	80	250	100	330	$\mu\text{S}$
$G_{OS}$ Output Conductance	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1\text{kHz}$		3		5		10	$\mu\text{S}$
$C_{iss}$ Input Capacitance	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		3		3		3	pF
$C_{rss}$ Reverse Transfer Capacitance	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		1.5		1.5		1.5	pF

### Typical 2N4117, 2N4118, 2N4119 Characteristics

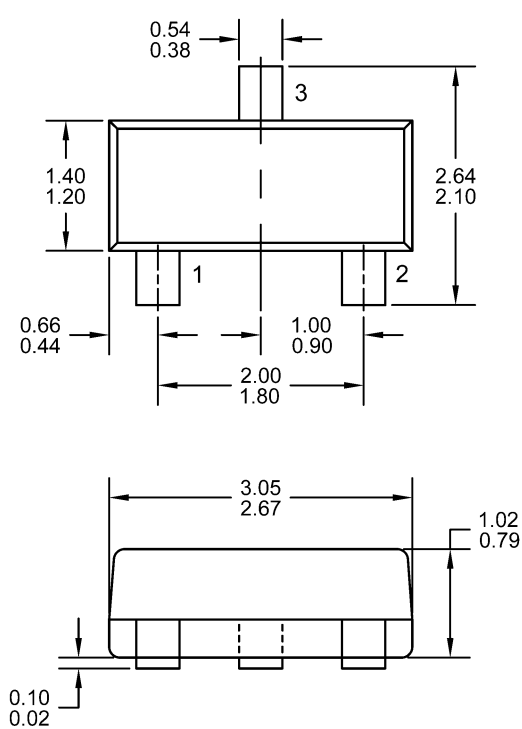


**Typical 2N4117, 2N4118, 2N4119 Characteristics (Continued)**



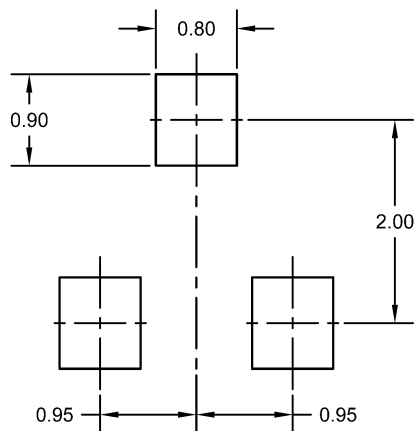
## SOT23 (TO-236AB) Mechanical and Layout Data

### Package Outline Data



1. All linear dimensions are in millimeters.
2. Package weight approximately 0.12 grams
3. Molded plastic case UL 94V-0 rated
4. For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
5. Bulk product is shipped in standard ESD shipping material
6. Refer to JEDEC standards for additional information.

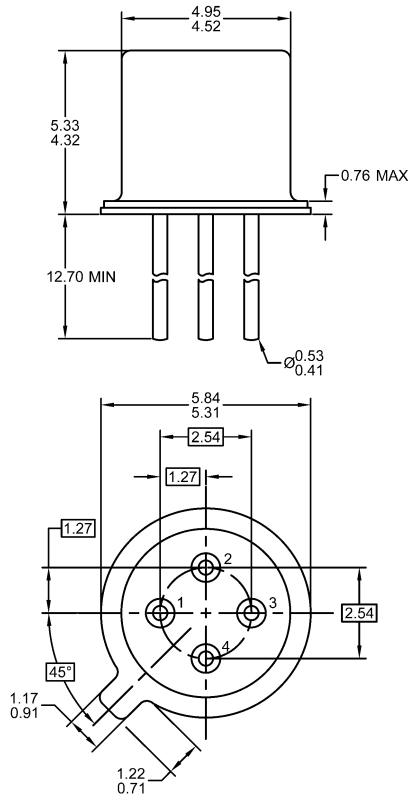
### Suggested Pad Layout



1. All linear dimensions are in millimeters.
2. The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.

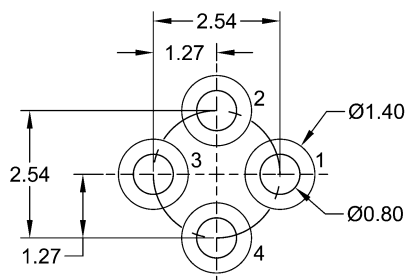
## TO-72 Mechanical and Layout Data

### Package Outline Data



1. All linear dimensions are in millimeters.
2. Four leaded device. Not all leads are shown in drawing views.
3. Package weight approximately 0.31 grams
4. Bulk product is shipped in standard ESD shipping material
5. Refer to JEDEC standards for additional information.

### Suggested Through-Hole Layout



1. All linear dimensions are in millimeters.
2. The suggested land pattern dimensions have been provided as a straight lead reference only. A more robust pattern may be desired for wave soldering and/or bent lead configurations.